TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

TC74HC132AP,TC74HC132AF,TC74HC132AFN

Quad 2-Input Schmitt NAND Gate

The TC74HC132A is a high speed CMOS 2-INPUT NAND SCHMITT TRIGGER GATE fabricated with silicon gate $\rm C^2MOS$ technology.

It achieves the high speed operation similar to equivalent LSTTL while maintaining the CMOS low power dissipation.

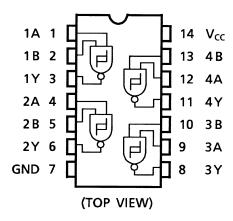
Pin configuration and function are the same as the TC74HC00A but the inputs have 25% $V_{\rm CC}$ hysteresis and with its schmitt trigger inputs, the TC74HC132A can be used as a line receiver for slow input signals.

All inputs are equipped with protection circuits against static discharge or transient excess voltage.

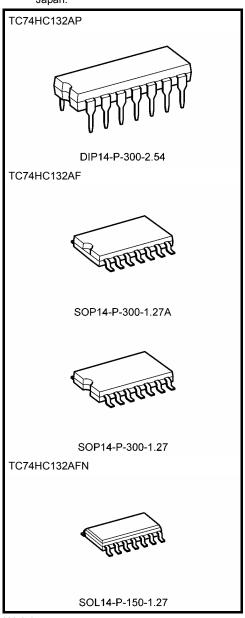
Features

- High speed: $t_{pd} = 11 \text{ ns (typ.)}$ at $V_{CC} = 5 \text{ V}$
- Low power dissipation: $I_{CC} = 1 \mu A \text{ (max)}$ at $T_{a} = 25 \text{°C}$
- High noise immunity: $V_H = 1.1 \text{ V}$ at $V_{CC} = 5 \text{ V}$
- Output drive capability: 10 LSTTL loads
- Symmetrical output impedance: |IOH| = IOL = 4 mA (min)
- Balanced propagation delays: $t_{pLH} \approx t_{pHL}$
- Wide operating voltage range: VCC (opr) = 2 to 6 V
- Pin and function compatible with 74LS132

Pin Assignment



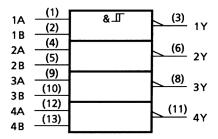
Note: xxxFN (JEDEC SOP) is not available in Japan.



Weight

DIP14-P-300-2.54 : 0.96 g (typ.) SOP14-P-300-1.27A : 0.18 g (typ.) SOP14-P-300-1.27 : 0.18 g (typ.) SOL14-P-150-1.27 : 0.12 g (typ.)

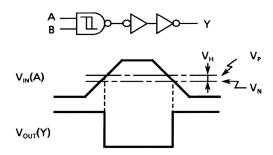
IEC Logic Symbol



Truth Table

Α	В	Υ
L	L	Н
L	Н	Н
Н	L	Н
Н	Н	L

System Diagram, Waveform



Absolute Maximum Ratings (Note 1)

Characteristics	Symbol	Rating	Unit
Supply voltage range	V _{CC}	–0.5 to 7	V
DC input voltage	V _{IN}	-0.5 to V _{CC} + 0.5	V
DC output voltage	V _{OUT}	-0.5 to V _{CC} + 0.5	V
Input diode current	l _{IK}	±20	mA
Output diode current	lok	±20	mA
DC output current	lout	±25	mA
DC V _{CC} /ground current	Icc	±50	mA
Power dissipation	PD	500 (DIP) (Note 2)/180 (SOP)	mW
Storage temperature	T _{stg}	−65 to 150	°C

Note 1: Exceeding any of the absolute maximum ratings, even briefly, lead to deterioration in IC performance or even destruction.

Note 2: 500 mW in the range of Ta = -40 to $65^{\circ}C$. From Ta = 65 to $85^{\circ}C$ a derating factor of -10 mW/°C shall be applied until 300 mW.



Recommended Operating Conditions (Note)

Characteristics	Symbol	Rating	Unit
Supply voltage	V_{CC}	2 to 6	V
Input voltage	V _{IN}	0 to V _{CC}	V
Output voltage	V _{OUT}	0 to V _{CC}	V
Operating temperature	T _{opr}	−40 to 85	°C

Note: The recommended operating conditions are required to ensure the normal operation of the device.

Unused inputs must be tied to either VCC or GND.

Electrical Characteristics

DC Characteristics

Characteristics Symbol		Test Condition $V_{CC}\left(V\right)$		Ta = 25°C			Ta = -40 to 85°C		Unit	
				Min	Тур.	Max	Min	Max	Onne	
		_		2.0	1.0	1.25	1.50	1.0	1.50	
Positive threshold voltage	V _P			4.5	2.3	2.70	3.15	2.3	3.15	V
Ğ				6.0	3.0	3.50	4.20	3.0	4.20	
				2.0	0.30	0.65	0.9	0.30	0.9	
Negative threshold voltage	V_N		_	4.5	1.13	1.60	2.0	1.13	2.0	V
				6.0	1.50	2.30	2.6	1.50	2.6	
				2.0	0.3	0.6	1.0	0.3	1.0	
Hysteresis output voltage	V_{H}	_		4.5	0.6	1.1	1.4	0.6	1.4	V
					0.8	1.2	1.7	0.8	1.7	
		.,		2.0	1.9	2.0	_	1.9	_	
			$I_{OH} = -20 \mu A$	4.5	4.4	4.5	_	4.4	_	
High-level output voltage	V _{OH}	V _{IN} = V _{IH} or V _{IL}		6.0	5.9	6.0	_	5.9	_	V
			$I_{OH} = -4 \text{ mA}$	4.5	4.18	4.31	_	4.13	_	
			$I_{OH} = -5.2 \text{ mA}$	6.0	5.68	5.80	_	5.63	_	
				2.0	_	0.0	0.1	_	0.1	
			$I_{OL} = 20 \mu A$	4.5	_	0.0	0.1	_	0.1	
Low-level output voltage VoL	V_{OL}	V _{IN} = V _{IH} or V _{IL}		6.0	_	0.0	0.1	_	0.1	V
			I _{OL} = 4 mA	4.5	_	0.17	0.26	_	0.33	
			$I_{OL} = 5.2 \text{ mA}$	6.0	_	0.18	0.26	_	0.33	
Input leakage current	I _{IN}	V _{IN} = V _{CC} or GND		6.0	_	_	±0.1	_	±1.0	μΑ
Quiescent supply current	I _{CC}	V _{IN} = V _{CC} or	GND	6.0		_	1.0		10.0	μΑ

AC Characteristics (C_L = 15 pF, V_{CC} = 5 V, Ta = 25°C, input: t_r = t_f = 6 ns)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Output transition time	t _{TLH}	_		4	8	ns
	t _{THL}			۲		110
Propagation delay time	t _{pLH}	_		11	18	ns
	t_{pHL}	_			10	110



AC Characteristics ($C_L = 50$ pF, input: $t_r = t_f = 6$ ns)

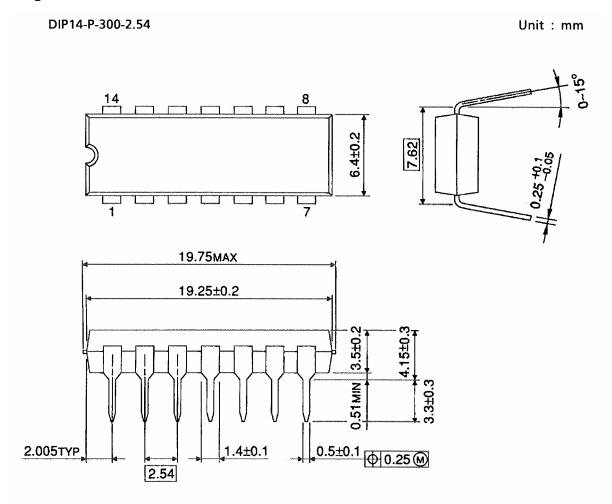
Characteristics	Symbol	Symbol Test Condition V _{CC} (V)		Ta = 25°C			Ta = -40 to 85°C		Unit
	- ,			Min	Тур.	Max	Min	Max	
	4 —		2.0	_	30	75	_	95	
Output transition time	t _{TLH}	_	4.5	_	8	15	_	19	ns
	t _{THL}		6.0	_	7	13	_	16	
	4		2.0	_	42	110	_	140	
Propagation delay time	t _{pLH}	_	4.5	_	14	22	_	28	ns
	t _{pHL}		6.0	_	12	19	_	24	
Input capacitance	C _{IN}	_		_	5	10	_	10	pF
Power dissipation	C _{PD}				29				pΕ
capacitance	(Note)				29				pF

Note: C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

$$I_{CC}$$
 (opr) = $C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/4$ (per gate)

Package Dimensions

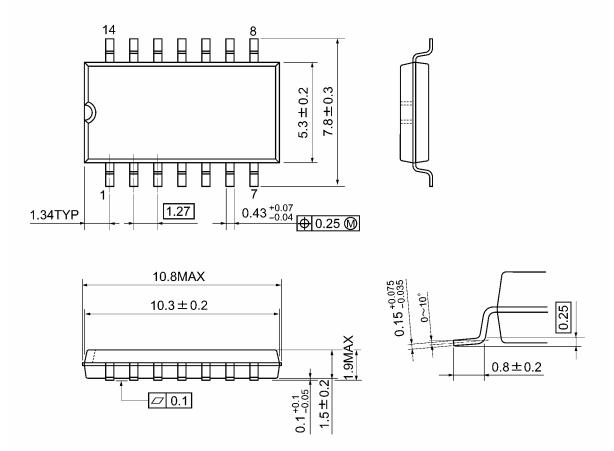


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Weight: 0.96 g (typ.)

Package Dimensions

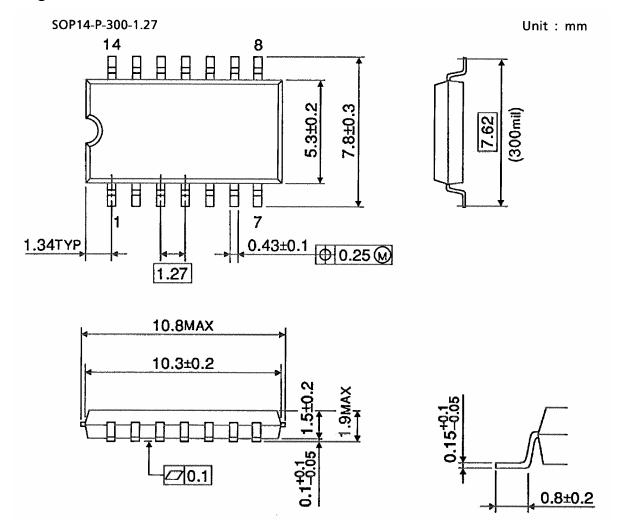
SOP14-P-300-1.27A Unit: mm



Weight: 0.18 g (typ.)



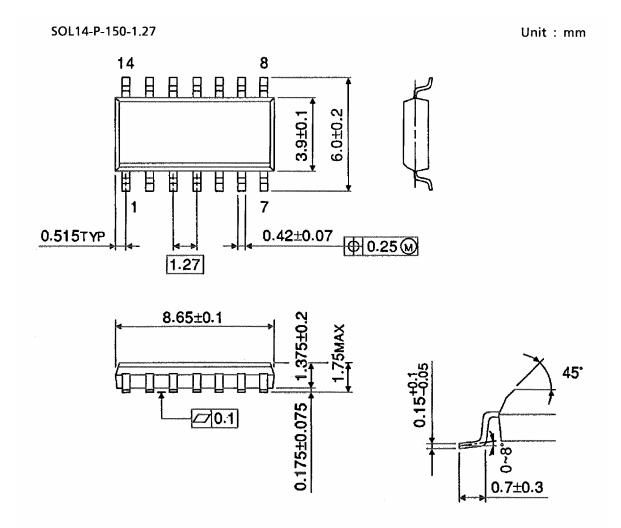
Package Dimensions



Weight: 0.18 g (typ.)



Package Dimensions (Note)



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Note: This package is not available in Japan.

Weight: 0.12 g (typ.)

Note: Lead (Pb)-Free Packages

DIP14-P-300-2.54 SOP14-P-300-1.27A SOL14-P-150-1.27

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